

SILICON NPN POWER DARLINGTON TRANSISTOR

- STMicrolectronics PREFERRED SALESTYPE
- HIGH GAIN
- NPN DARLINGTON
- HIGH CURRENT
- HIGH DISSIPATION
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

APPLICATIONS

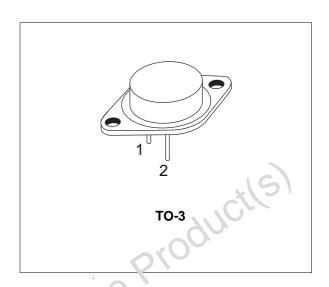
 LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

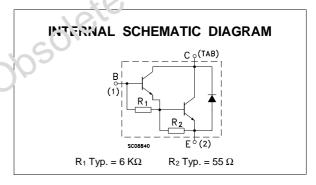
DESCRIPTION

The 2N6059 is a silicon Epitaxial-Base NPN transistor in monolithic Darlington configuration mounted in Jedec TO-3 metal case.

It is inteded for use in power linear and low frequency switching applications.

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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
VOBO	Collector-Base Voltage (I _E = 0)	100	V
/ _{CEX}	Collector-Emitter Voltage (V _{BE} = -1.5V)	100	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	100	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	5	V
Ic	Collector Current	12	А
I _{CM}	Collector Peak Current (tp < 5 ms)	20	А
Ι _Β	Base Current	0.2	А
P _{tot}	Total Dissipation at T _c ≤ 25 °C	150	W
T _{stg}	Storage Temperature	-65 to 200	°C
Tj	Max. Operating Junction Temperature	200	°C

February 2003

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.17	°C/W	
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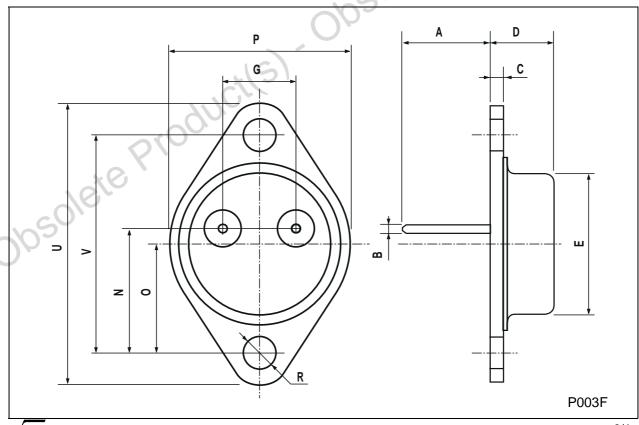
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

I_{CEX}	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
	Collector Cut-off Current (V _{BE} = -1.5V)	V_{CE} = rated V_{CEX} V_{CE} = rated V_{CEX} T_c = 150 $^{\circ}$ C			0.5 5	mA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 50 V			1	mA
I _{EBO}	Emitter Cut-off Current (Ic = 0)	V _{EB} = 5 V			2	mA
$V_{CEO(sus)^*}$	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	100			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 6 A I _B = 24 mA I _C = 12 A I _B = 120 mA			2 3	V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 12 A I _B = 120 mA			4	7
V _{BE} *	Base-Emitter Voltage	I _C = 6 A V _{CE} = 3 V		All	2.8	V
h _{FE} *	DC Current Gain	Ic = 6 A	750 100	0,		
f _T	Transition frequency	I _C = 5 A V _{CE} = 3 V f = 1 MHz	4			MH
		0,5				
		.(5)				
	codu	cilsi				
	Produ	cils				
	ste Produ	cilo				
0501	ste Produ	I _C = 5 A V _{CE} = 3 V f = 1 MHz 5 %				

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TO-3 MECHANICAL DATA

DIM.	mm		inch			
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	11.00		13.10	0.433		0.516
В	0.97		1.15	0.038		0.045
С	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
Е	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
Р	25.00		26.00	0.984	401	1.023
R	4.00		4.09	0.157	2400	0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



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